

Silicon NPN Power Transistors

BU908

DESCRIPTION

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- With TO-3PN package
- High voltage
- High speed switching

APPLICATIONS

- For color TV horizontal deflection circuits.

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

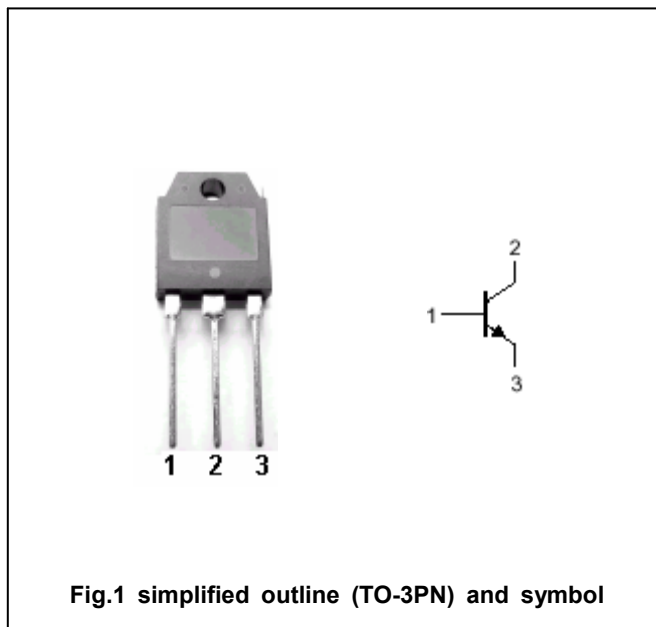


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	700	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		8	A
P _T	Total power dissipation	T _C =25°C	125	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-65~150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance junction case	1.0	°C/W

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CHARACTERISTICS

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 $T_j=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	$I_C=100\text{mA}; I_B=0;$	700			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=10\text{mA}; I_C=0;$	7			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=3.2\text{A}; I_B=0.8\text{A}$			2.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=3.2\text{A}; I_B=0.8\text{A}$			1.3	V
I_{CBO}	Collector cut-off current	$V_{CB}=1500\text{V}; I_E=0$			1.0	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=5\text{V}; I_C=0$			0.1	mA
h_{FE}	DC current gain	$I_C=1.5\text{A}; V_{CE}=5\text{V}$	8			
f_T	Transition frequency	$I_E=0; V_{CB}=10\text{V}; f=1\text{MHz}$		7		MHz

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PACKAGE OUTLINE

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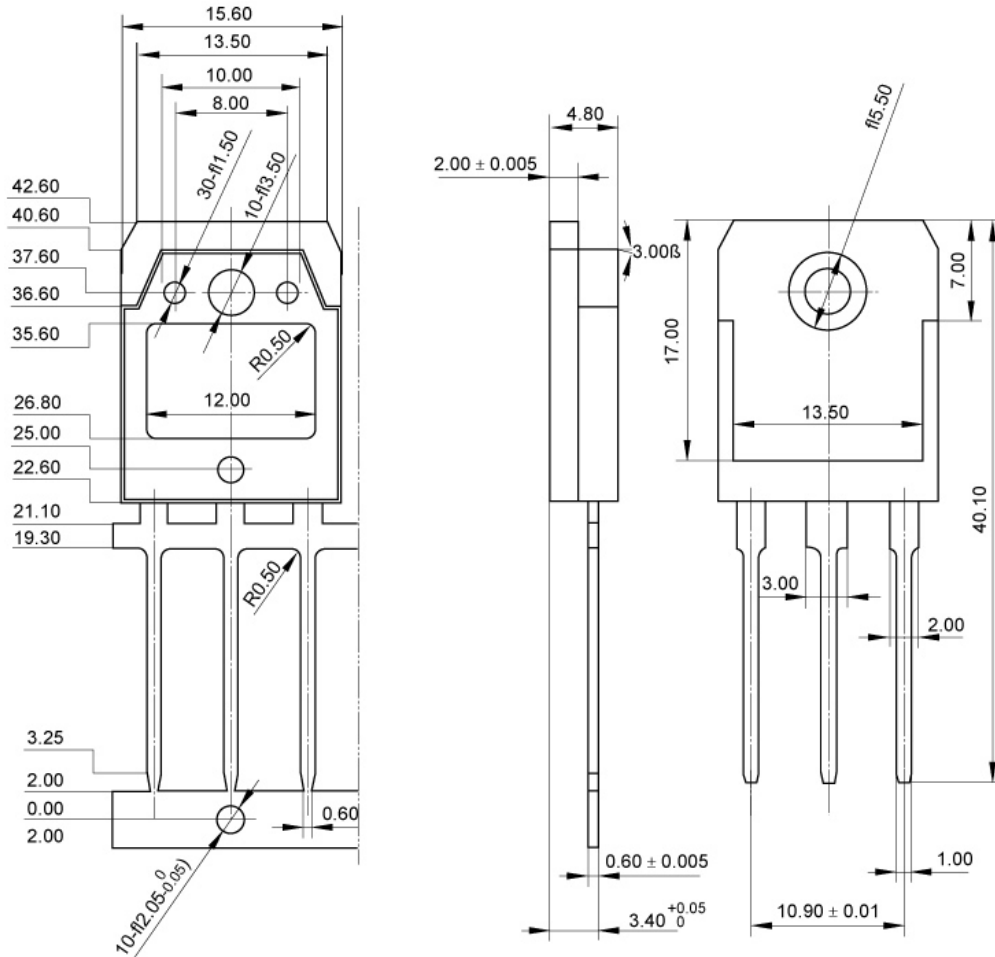


Fig.2 outline dimensions (unindicated tolerance:±0.10 mm)